

S3D120V035S SiC Schottky Diode

Features:

- 1200V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient
- Temperature independent Switching

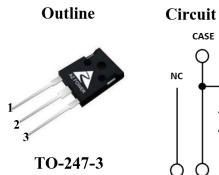
Applications:

- Switch Mode Power Supply
- Booster diodes in PFC, DC/DC
- AC/DC converters

Benefits:

- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

Symbol	Value	Unit		
V _{RRM}	1200	V		
$I_F \ (Te=139^{o}C)$	35	А		
Qc	286	nC		



Symbol	Parameter	Value	Unit	Test Conditions
V _R	DC Peak Reverse Voltage	1200	v	$T_J = 25^{\circ}C$
V _{RRM}	Repetitive Peak Reverse	1200	V	$T_J = 25^{\circ}C$
V _{RSM}	Surge Peak Reverse Voltage	1300	V	$T_J = 25^{\circ}C$
I _F	Continuous Forward Current	82 65 35	A	$T_{C} = 25^{\circ}C$ $T_{C} = 75^{\circ}C$ $T_{C} = 139^{\circ}C$
I _{FRM}	Repetitive Peak Forward Surge Current	292 158	А	$T_{\rm C} = 25^{\circ}$ C, $T_{\rm P} = 10$ ms, Half Sine Wave Tc = 110°C, $T_{\rm P} = 10$ ms, Half Sine Wave
I _{FSM}	Non-Repetitive Peak Forward Surge Current	338 285	А	$T_{C} = 25^{\circ}C$, $T_{P} = 10ms$, Half Sine Wave Tc = 110°C, $T_{P} = 10ms$, Half Sine Wave
PD	Power Dissipation	326 108	W	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 125^{\circ}{\rm C}$
T _{J,max}	Operating Junction Temperature	175	°C	
T _{stg}	Storage Temperature Range	-55 to 175	°C	

Maximum Ratings

S3D120V035S, Rev. 1.0

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Thermal characteristics

Symbol	Parameter	Min.	Тур.	Max.	Unit
RthJC	Thermal resistance		0.46		°C/W

Electrical Characteristics

Symbol	Dovomotor		Value		Unit	Test Conditions	
Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions	
V _{DC}	DC Blocking Voltage	1200			V	$I_R = 200 \mu A, T_J = 25^{\circ}C$	
V _F	Forward Voltage		1.45	1.7	v	$I_F = 35A, T_J = 25^{\circ}C$	
v F	Forward Voltage		2.2	2.5		$I_F = 35A, T_J = 175^{\circ}C$	
I.	Reverse Current		10	200	μΑ	$V_{R} = 1200V, T_{J} = 25^{\circ}C$	
I _R	Reverse Current		50	1000		$V_R = 1200V, T_J = 175^{\circ}C$	
0	Tetal Courseiting Change		296		nC	C	$I_{\rm F}$ = 35A, dI/dt = 550A/µs
Qc	Total Capacitive Charge		286			$T_J = 25^{\circ}C, V_R = 800V$	
			1810		pF	$V_{R} = 1V, T_{J} = 25^{\circ}C, f = 1 \text{ MHz}$	
С	Total Capacitance		256			V_R =400V, T_J =25°C, f=1 MHz	
			201			V_R =800V, T_J =25°C, f=1 MHz	

Typical Performance

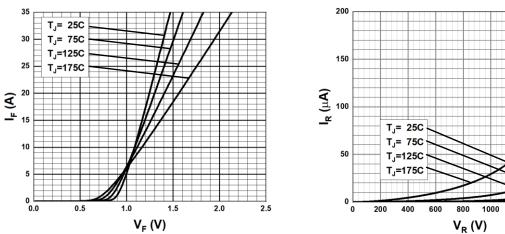
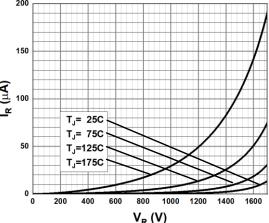


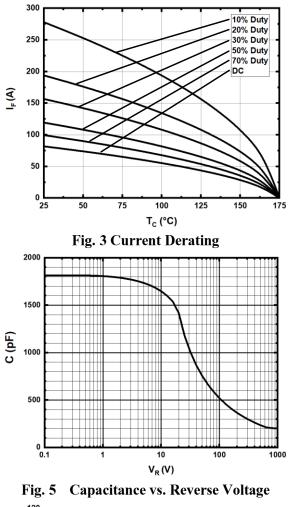
Fig. 1 Forward Characteristics







Typical Performance



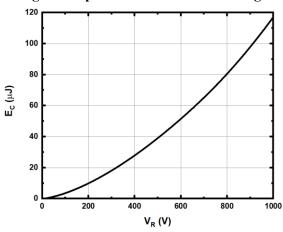


Fig. 7 Capacitance stored Energy

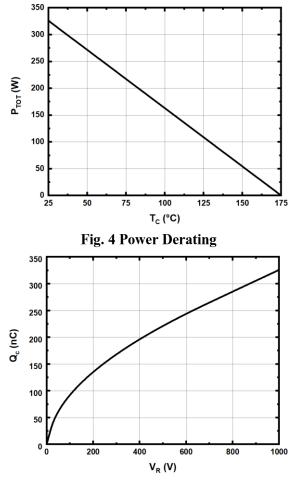


Fig. 6 Recovery Charge vs. Reverse Voltage

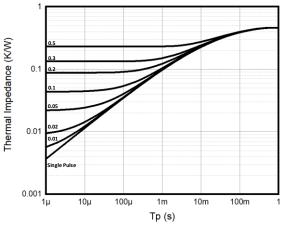
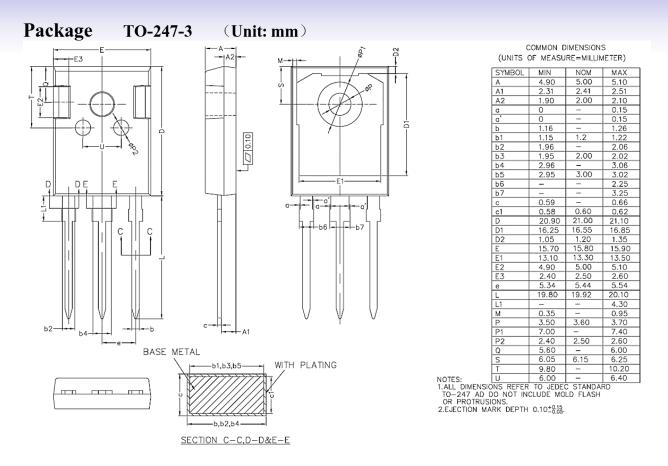


Fig. 8 Transient Thermal Impedance





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